

S/N 08/903,453

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes et al.

Examiner: V. Martin Wallace

Serial No.: 08/903,453

Group Art Unit: 2815

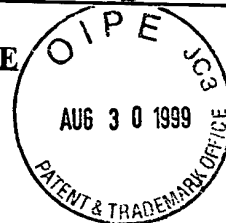
Filed: July 29, 1997

Docket: 303.378US1

Title: CARBURIZED SILICON GATE INSULATORS FOR INTEGRATED CIRCUITS

AMENDMENT AND RESPONSE

Assistant Commissioner for Patents
Washington, D.C. 20231



13/C
Smalley
9-17-99

In response to the Office Action mailed April 27, 1999, please amend the above-identified application as follows.

IN THE CLAIMS

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Please amend the claims as follows:

ISEP 02 1999

TECHNOLOGY CENTER 2800

3.(Amended) An integrated circuit memory device supported by a semiconductor substrate, the device comprising:

- a source and a drain separated by a channel supported by a semiconductor substrate;
- a floating gate supported by the substrate and extending between the source and drain above the channel;
- a control gate formed adjacent to and insulated from the floating gate; and
- an insulative layer of amorphous carburized silicon formed between the channel and the floating gate.

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4.(Amended) An integrated circuit capacitor supported by a semiconductor substrate, the capacitor comprising:

- a first conductor layer supported by the substrate;
- a dielectric layer of amorphous carburized silicon formed on top of the first conductor layer; and
- a second conductor layer formed on top of the dielectric layer.

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